

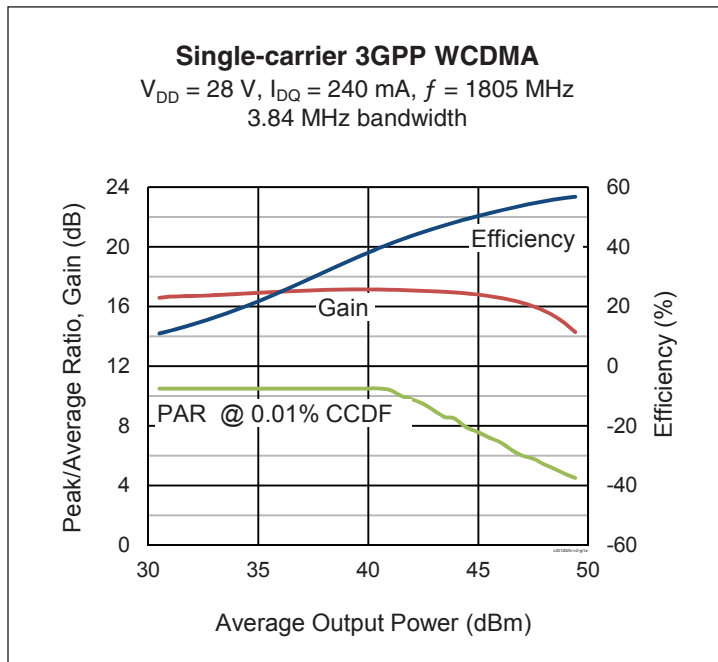
Thermally-Enhanced High Power RF LDMOS FET 120 W, 28 V, 1800 – 2200 MHz

Description

The PXAC201202FC is a 120-watt LDMOS FET for use in multi-standard cellular power amplifier applications in the 1800 to 2200 MHz frequency band. Its asymmetric and dual-path design make it ideal for Doherty amplifier designs. It features input and output matching, and a thermally-enhanced package with earless flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



PXAC201202FC
Package H-37248-4



Features

- Broadband internal matching
- Asymmetric Doherty design
 - Main: P1dB = 35 W Typ
 - Peak: P1dB = 80 W Typ
- Broadband internal matching
- CW performance in a Doherty configuration, 1805 MHz, 28 V
 - Output power = 100 W P_{1dB}
 - Gain = 17.3 dB at 17.8 W Avg.
 - Efficiency = 46% at 17.8 W Avg.
- CW performance in a Doherty configuration, 2100 MHz, 28 V
 - Output power = 15.8 W Avg.
 - Gain = 15.5 dB
 - Efficiency = 46%
- Capable of handling 10:1 VSWR @ 28 V, 16 W (CW) output power
- Integrated ESD protection: Human Body Model, Class 1C (per JESD22-A114)
- Low thermal resistance
- Pb-free and RoHS compliant

RF Specifications, 1880 MHz

One-carrier WCDMA Characteristics (tested in Infineon Doherty test fixture)

$V_{DD} = 28\text{ V}$, $V_{GS(peak)} = 1.4\text{ V}$, $I_{DQ} = 240\text{ mA}$, $P_{OUT} = 16\text{ W}$ average, $f = 1880\text{ MHz}$. 3GPP WCDMA signal: 3.84 MHz bandwidth, 10 dB PAR @0.01% probability on CCDF.

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	16	17	—	dB
Drain Efficiency	η_D	43	46	—	%
Adjacent Channel Power Ratio	ACPR	—	-29	-26	dBc

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

RF Specifications, 2140 MHz

One-carrier WCDMA Characteristics (not subject to production test—verified by design/characterization in Infineon Doherty test fixture)

$V_{DD} = 28\text{ V}$, $V_{GS(\text{peak})} = 1.2\text{ V}$, $I_{DQ} = 240\text{ mA}$, $P_{OUT} = 16\text{ W}$ average, $f = 2140\text{ MHz}$. 3GPP WCDMA signal: 3.84 MHz bandwidth, 10 dB PAR @0.01% CCDF.

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	16.0	16.5	—	dB
Drain Efficiency	η_D	39	42	—	%
Adjacent Channel Power Ratio	ACPR	—	-29	-27	dBc

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1.0	μA
	$V_{DS} = 63\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	10.0	μA
Gate Leakage Current	$V_{GS} = 10\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	—	1.0	μA
On-state Resistance	(main) $V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(\text{on})}$	—	0.3	—	Ω
	(peak) $V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(\text{on})}$	—	0.16	—	Ω
Operating Gate Voltage	(main) $V_{DS} = 28\text{ V}$, $I_{DQ} = 242\text{ mA}$	V_{GS}	2.5	2.69	2.8	V
	(peak) $V_{DS} = 28\text{ V}$, $I_{DQ} = 0\text{ A}$	V_{GS}	0.5	0.7	1.6	V

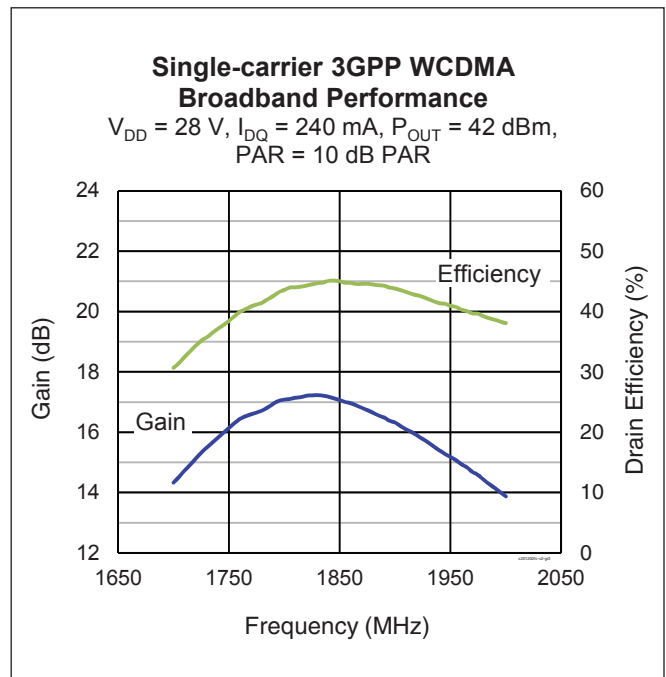
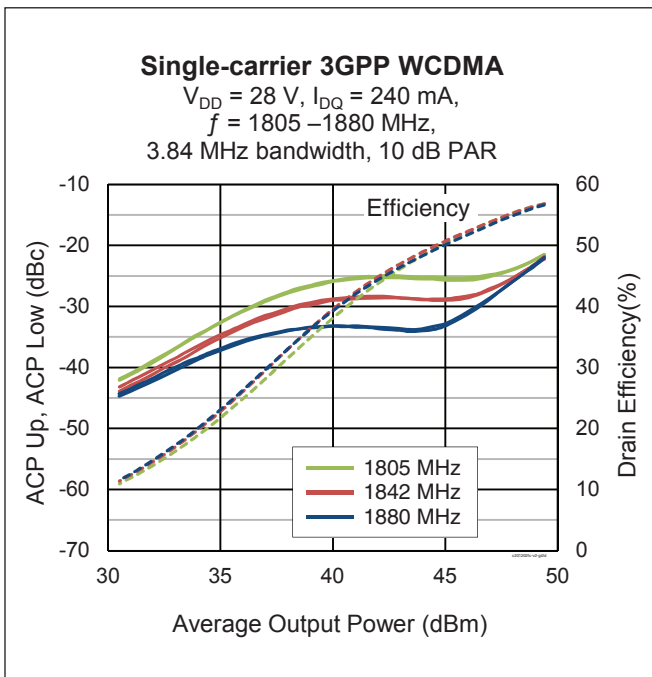
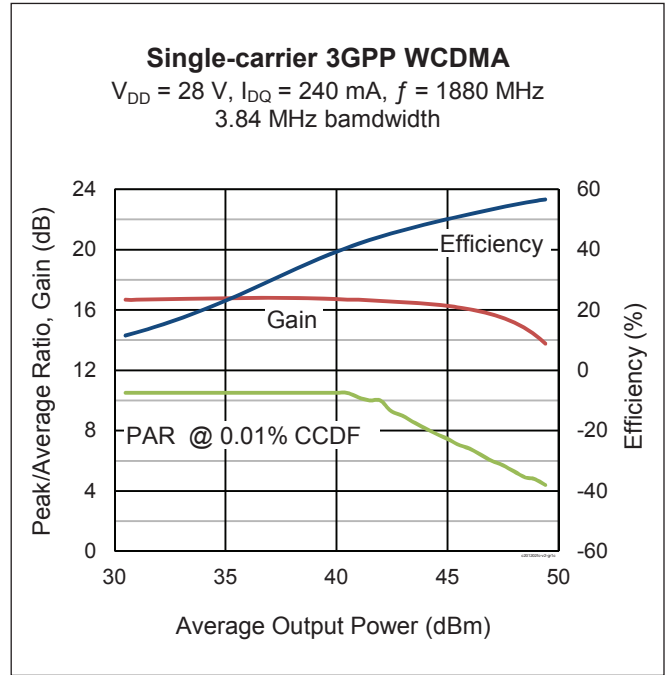
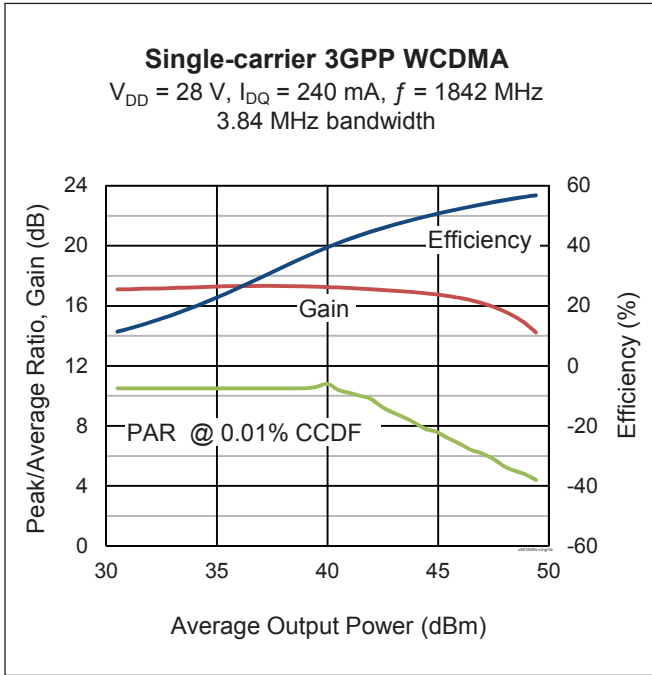
Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source Voltage	V_{DSS}	65	V
Gate-source Voltage	V_{GS}	-6 to +10	V
Operating Voltage	V_{DD}	0 to +32	V
Junction Temperature	T_J	225	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance ($T_{CASE} = 70^{\circ}\text{C}$, 100 W CW)	$R_{\theta JC}$	0.7	$^{\circ}\text{C/W}$

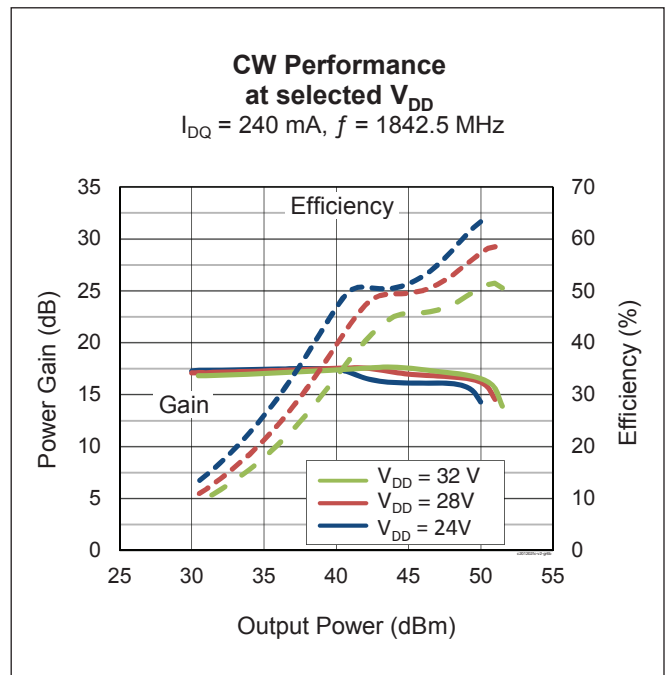
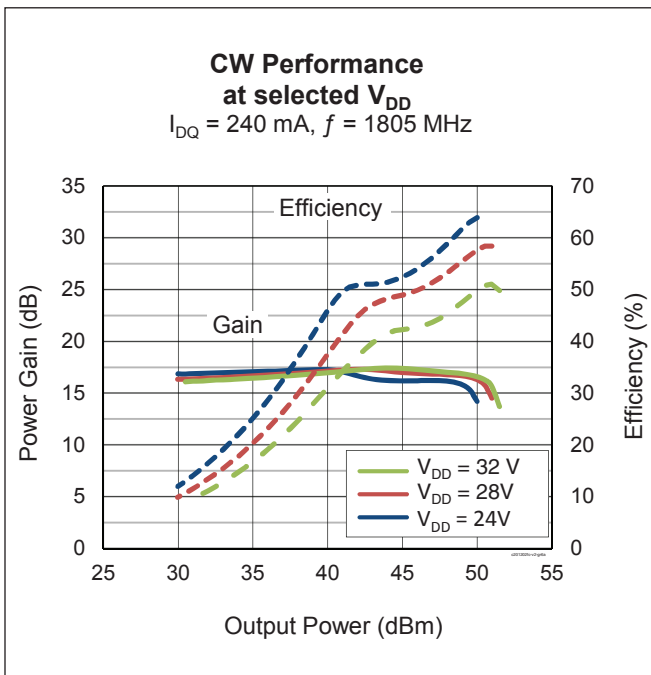
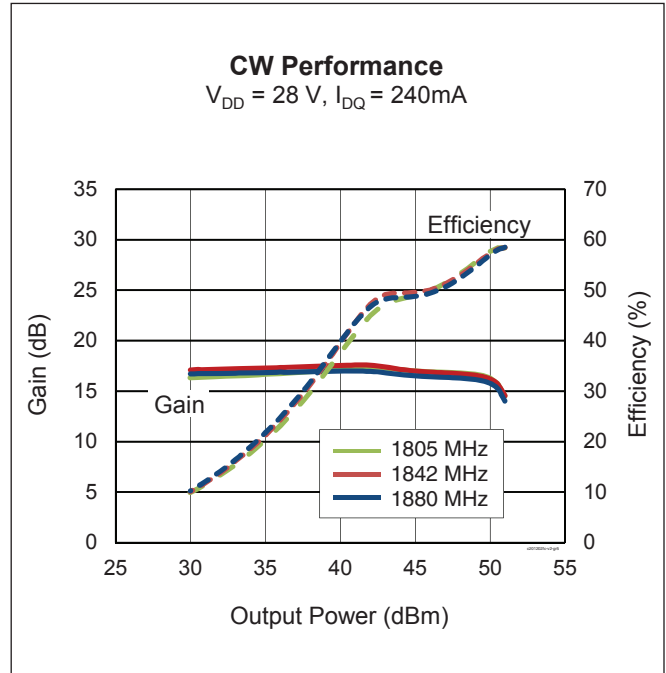
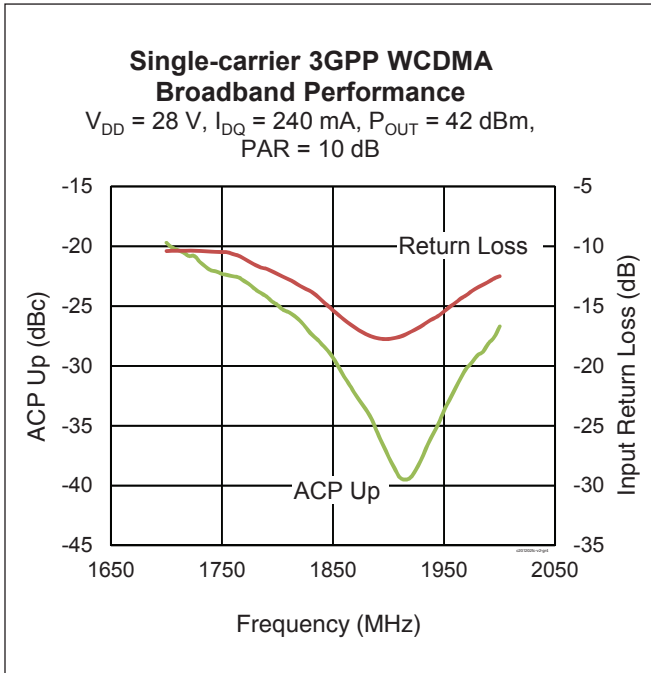
Ordering Information

Type and Version	Order Code	Package and Description	Shipping
PXAC201202FC V2 R0	PXAC201202FCV2R0XTMA1	H-37248-4, ceramic open-cavity, earless	Tape & Reel, 50 pcs
PXAC201202FC V2 R250	PXAC201202FCV2R250XTMA1	H-37248-4, ceramic open-cavity, earless	Tape & Reel, 250 pcs

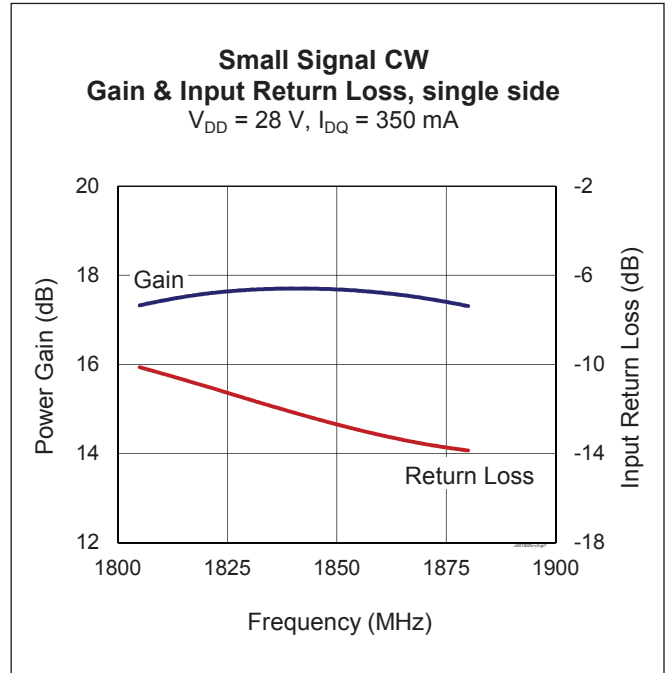
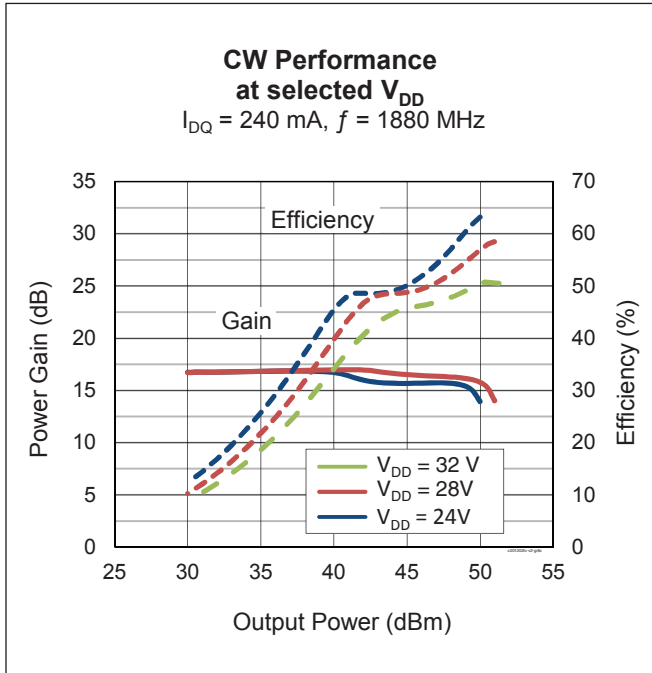
Typical Performance (data taken in an Infineon test fixture)



Typical Performance (cont.)

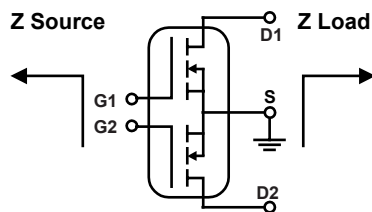


Typical Performance (cont.)



See next page for load pull performance

Load Pull Performance



Main side pulsed CW signal: 160 μ sec, 10% duty cycle; 28 V, 250 mA

Class AB		P _{1dB}					P _{1dB}				
		Max Output Power					Max PAE				
Freq [MHz]	Z _s [Ω]	Z _l [Ω]	Gain [dB]	P _{OUT} [dBm]	P _{OUT} [W]	PAE [%]	Z _l [Ω]	Gain [dB]	P _{OUT} [dBm]	P _{OUT} [W]	PAE [%]
1810	3.92 – j12.74	8.74 – j8.12	19.55	46.79	47.75	53.6	14.51 – j15.32	21.55	45.00	31.65	62.1
1840	4.13 – j12.84	8.56 – j7.87	19.43	46.58	45.50	52.3	15.46 – j14.87	21.52	44.81	30.28	61.3
1880	4.54 – j14.31	8.66 – j8.19	19.37	46.92	49.20	55.3	18.77 – j12.73	21.53	45.05	31.98	65.2

Peak side pulsed CW signal: 160 μ sec, 10% duty cycle; 28 V, 540 mA

Class AB		P _{1dB}					P _{1dB}				
		Max Output Power					Max PAE				
Freq [MHz]	Z _s [Ω]	Z _l [Ω]	Gain [dB]	P _{OUT} [dBm]	P _{OUT} [W]	PAE [%]	Z _l [Ω]	Gain [dB]	P _{OUT} [dBm]	P _{OUT} [W]	PAE [%]
1810	3.75 – j8.61	2.62 – j5.15	18.47	49.89	97.50	48.3	4.96 – j7.28	20.92	48.49	70.63	59.9
1840	3.69 – j8.66	2.99 – j4.99	19.05	49.85	96.61	51.0	5.17 – j6.42	20.80	48.71	74.30	59.2
1880	5.57 – j9.39	3.09 – j5.13	19.31	50.12	102.8	50.1	6.31 – j6.59	21.34	48.55	71.61	63.2

Reference Circuit, 1880 MHz

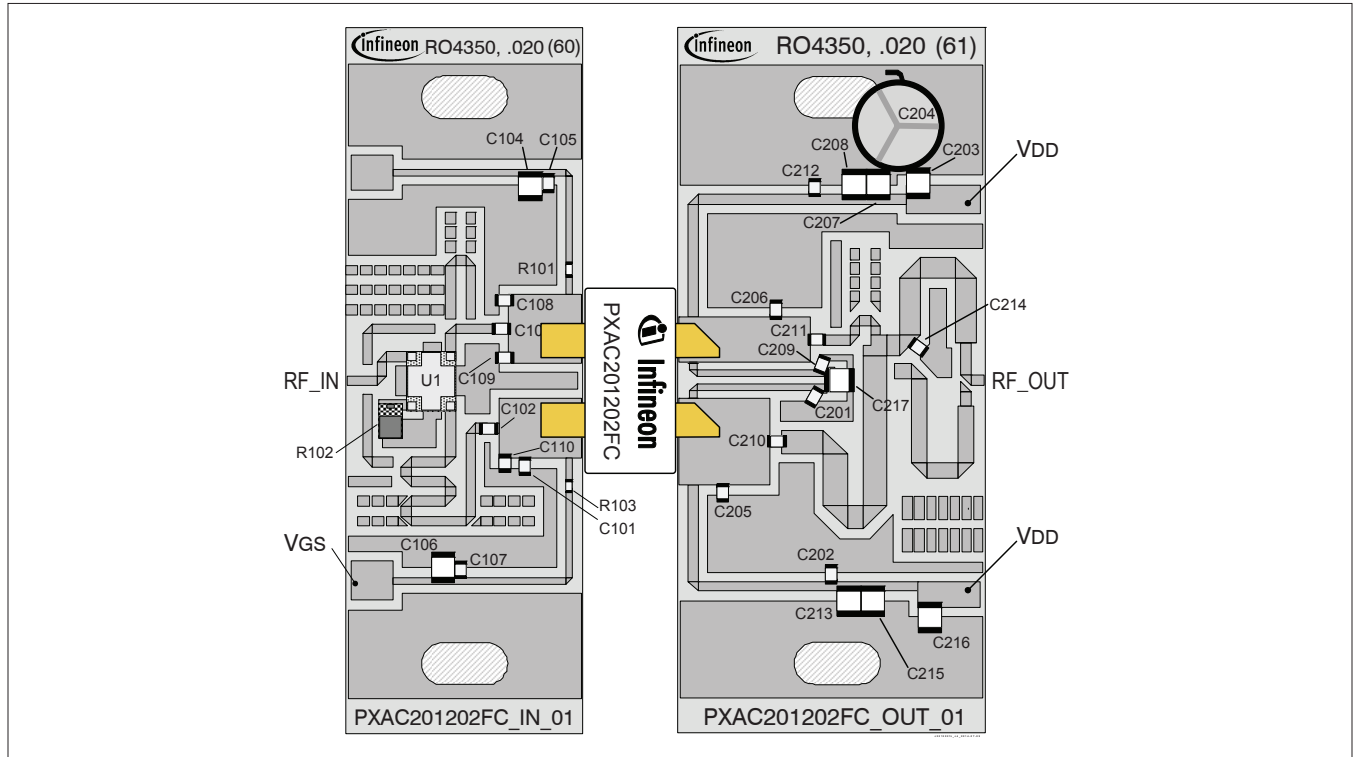
DUT PXAC201202FC V2

Reference Circuit Part No. LTA/PXAC201202FC V2

PCB Rogers 4350, 0.508 mm [.020"] thick, 2 oz. copper, $\epsilon_r = 3.66$

Find Gerber files for this reference fixture on the Infineon Web site at (www.infineon.com/rfpower)

Reference Circuit (cont.)

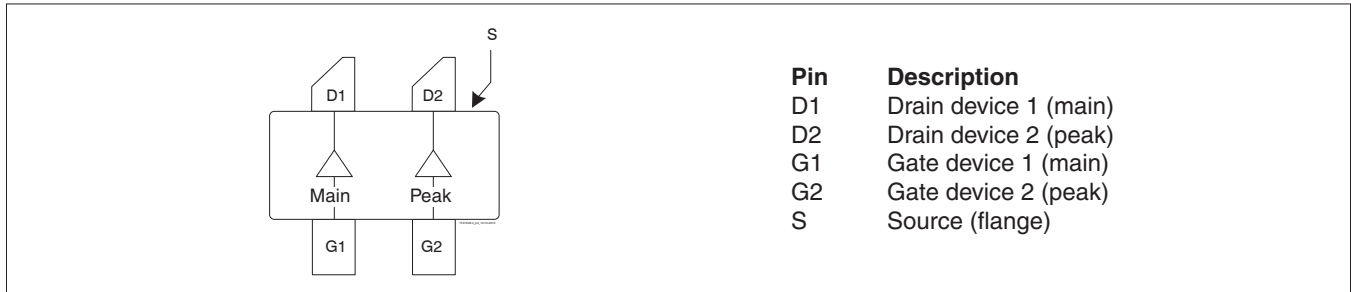


Reference circuit assembly diagram (not to scale)

Component Information

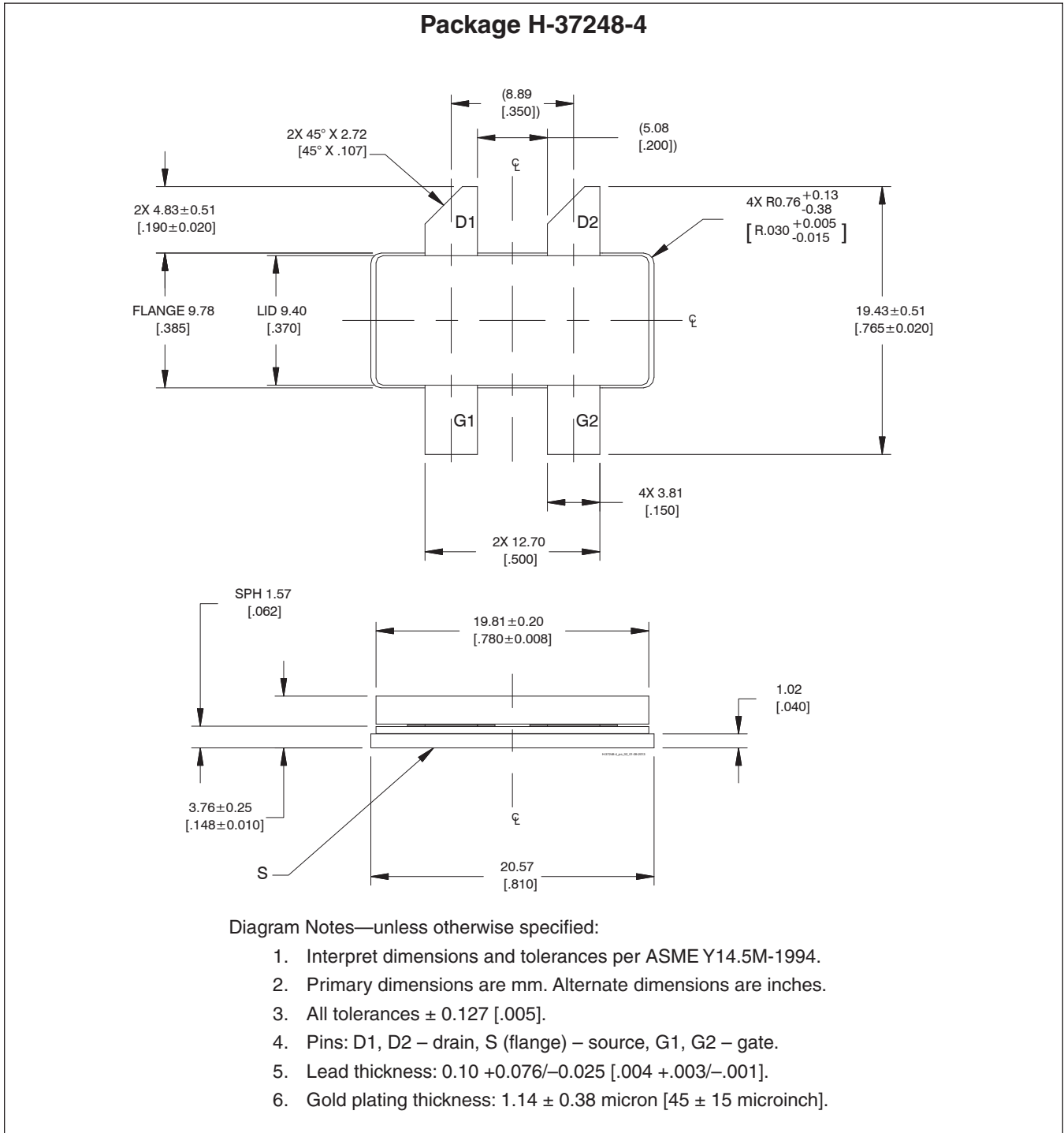
Component	Description	Manufacturer	P/N
Input			
C101	Chip capacitor, 2.2 pF	ATC	ATC600F2R2CW250T
C102, C105, C107	Chip capacitor, 18 pF	ATC	ATC600F180JW250T
C103	Chip capacitor, 1.5 pF	ATC	ATC600F1R5CW250T
C104, C106	Capacitor, 10 μF, 50 V	Taiyo Yuden	UMK325C7106MM-T
C108	Chip capacitor, 0.3 pF	ATC	ATC600F0R3CW250T
C109, C110	Chip capacitor, 0.3 pF	ATC	ATC600F0R3CW250T
R101, R103	Resistor, 10 Ohm	Panasonic Electronic Components	ERJ-3GEYJ
R102	Resistor, 50 Ohm	Anaren	RFP060120A15Z50
U1	Hybrid coupler, 5 dB, 90°	Anaren	X3C19P1-05S
Output			
C201, C202, C209, C210, C211, C212	Chip capacitor, 18 pF	ATC	ATC600F180JW250T
C203, C207, C208, C213, C215, C216, C217	Capacitor, 10 μF, 50 V	Taiyo Yuden	UMK325C7106MM-T
C204	Capacitor, 220 μF, 50 V	Cornell Dubilier Electronics (CDE)	SK221M050ST
C205	Chip capacitor, 1.8 pF	ATC	ATC600F1R8CW250T
C206	Chip capacitor, 0.3 pF	ATC	ATC600F0R3CW250T
C214	Chip capacitor, 0.5 pF	ATC	ATC600F0R5CW250T

Pinout Diagram (top view)



See next page for package mechanical specifications

Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page (www.infineon.com/rfpower)

Revision History

Revision	Date	Data Sheet	Page	Subjects (major changes in comparison with previous revision)
01	2014-02-06	Advance	All	New product, proposed only.
02	2014-03-07	Production	All	Data Sheet reflects released product specifications, including reference circuit and performance information.
03	2014-03-12	Production	1, 2, 3, 6	(1) Add features, update graph. (2) Update Operating Gate Voltage. (3) Update two graphs. (6) Add Load Pull tables.
04	2014-06-27	Production	All	Product now V2.
04.1	2014-08-25	Production	7	Assembly diagram: position of C201 changed.
05	2014-08-25	Production	2	RF Specifications at 2140 MHz: values updated.
05.1	2016-06-22	Production	2	Updated ordering information

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

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